

High-Gain IGBTs

IXGA50N60C4

IXGP50N60C4

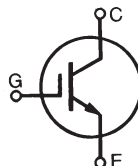
IXGH50N60C4

$V_{CES} = 600V$

$I_{C110} = 46A$

$V_{CE(sat)} \leq 2.3V$

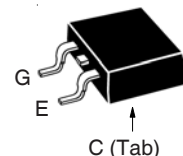
High-Speed PT Trench IGBT



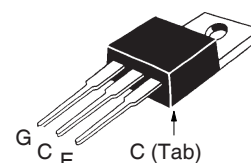
Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^{\circ}C$ to $150^{\circ}C$	600	V
V_{CGR}	$T_J = 25^{\circ}C$ to $150^{\circ}C$, $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^{\circ}C$	90	A
I_{C110}	$T_C = 110^{\circ}C$	46	A
I_{CM}	$T_C = 25^{\circ}C$, 1ms	220	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^{\circ}C$, $R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 72$ $V_{CE} \leq V_{CES}$	A
P_C	$T_C = 25^{\circ}C$	300	W
T_J		-55 ... +150	$^{\circ}C$
T_{JM}		150	$^{\circ}C$
T_{stg}		-55 ... +150	$^{\circ}C$
T_L	Maximum Lead Temperature for Soldering	300	$^{\circ}C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^{\circ}C$
F_C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
M_d	Mounting Torque (TO-220 & TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

Symbol	Test Conditions ($T_J = 25^{\circ}C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^{\circ}C$			25 μA 1 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 36A$, $V_{GE} = 15V$, Note 1 $T_J = 125^{\circ}C$	1.9 1.6		2.3 V V

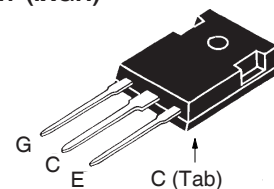
TO-263 AA (IXGA)



TO-220AB (IXGP)



TO-247 (IXGH)



G = Gate D = Collector
S = Emitter Tab = Collector

Features

- Optimized for Low Switching Losses
- International Standard Packages
- Square RBSOA

Advantages

- Easy to Mount
- Space Savings

Applications

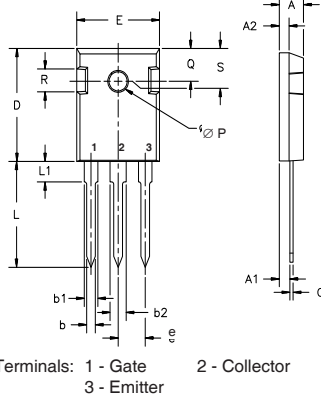
- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Lamp Ballasts

Symbol Test Conditions
 $(T_J = 25^\circ\text{C Unless Otherwise Specified})$
Characteristic Values

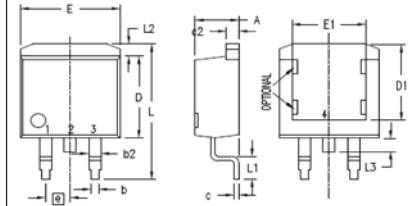
		Min.	Typ.	Max.
g_{fs}	$I_C = 36\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	20	30	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1900	pF
C_{oes}			100	pF
C_{res}			60	pF
Q_g	$I_C = I_{C110}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		113	nC
Q_{ge}			13	nC
Q_{gc}			44	nC
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ\text{C}$ $I_C = 36\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 10\Omega$ Note 2		40	ns
t_{ri}			66	ns
E_{on}			0.95	mJ
$t_{d(off)}$			270	ns
t_{fi}			63	ns
E_{off}			0.84	mJ
$t_{d(on)}$	Inductive Load, $T_J = 125^\circ\text{C}$ $I_C = 36\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 10\Omega$ Note 2		30	ns
t_{ri}			45	ns
E_{on}			1.10	mJ
$t_{d(off)}$			210	ns
t_{fi}			96	ns
E_{off}			0.90	mJ
R_{thJC}				0.42 $^\circ\text{C/W}$
R_{thCS}	TO-247		0.21	$^\circ\text{C/W}$
	TO-220		0.50	$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

TO-247 Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

TO-263 Outline


- 1 = Gate
- 2 = Collector
- 3 = Emitter
- 4 = Collector

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A ₁	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b ₂	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c ₂	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D ₁	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E ₁	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L ₁	.090	.110	2.29	2.79
L ₂	.040	.055	1.02	1.40
L ₃	.050	.070	1.27	1.78
L ₄	0	.005	0	0.13

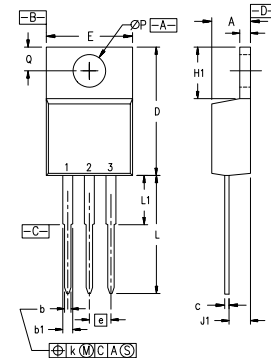
TO-220 Outline


Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

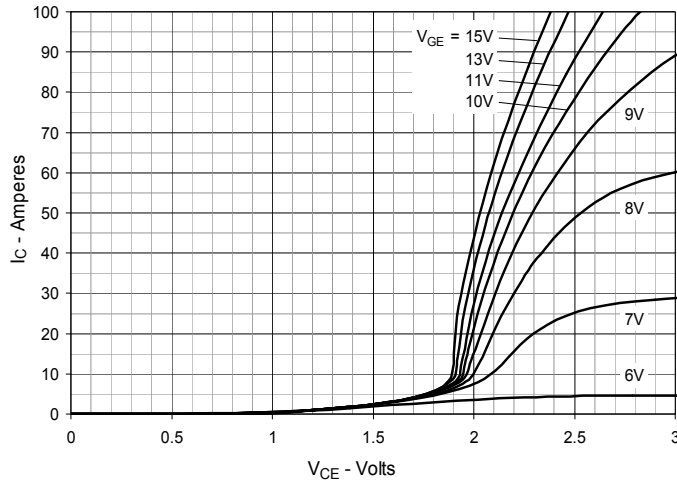


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

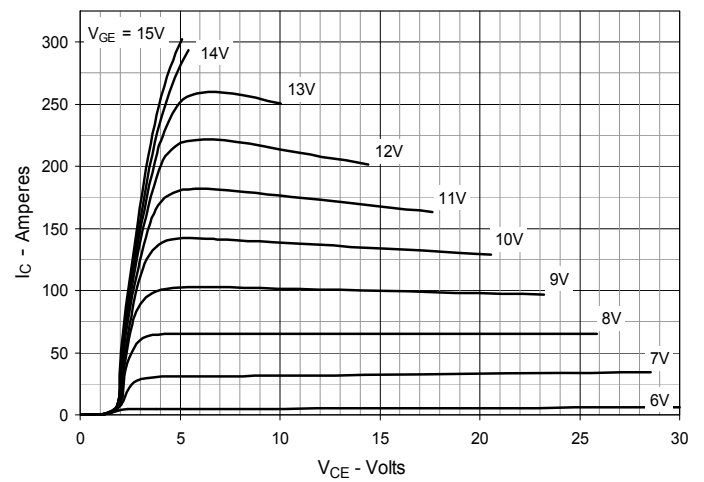


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

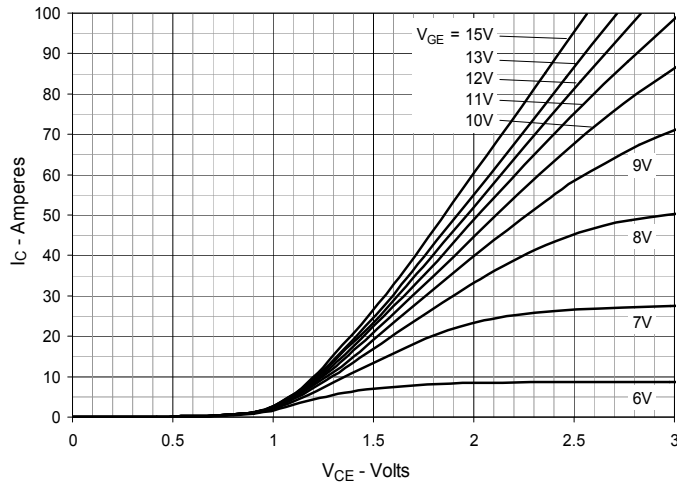


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

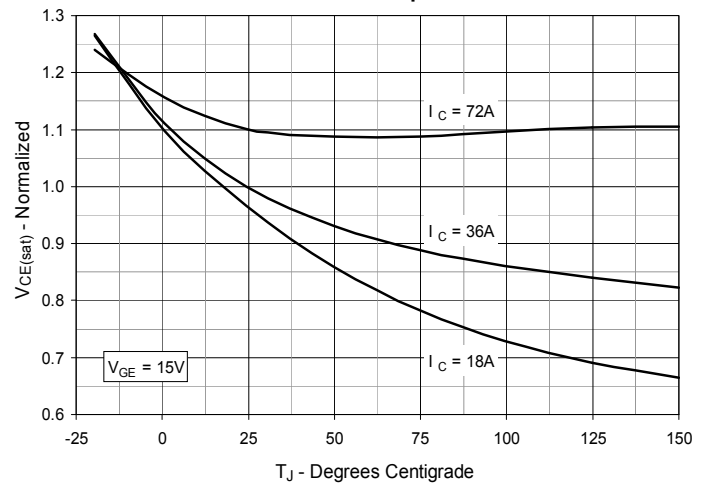


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

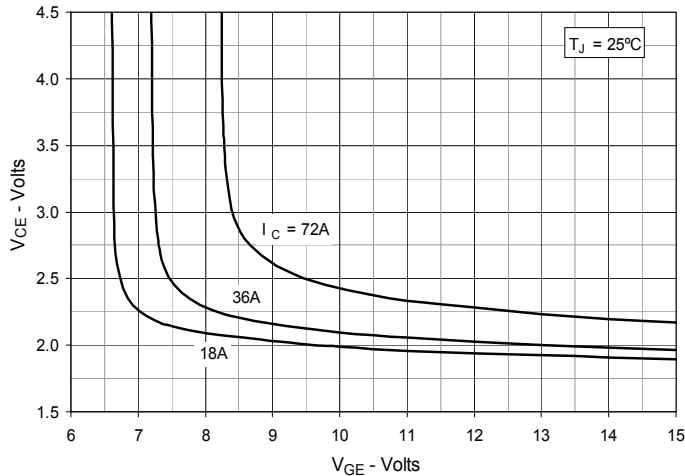


Fig. 6. Input Admittance

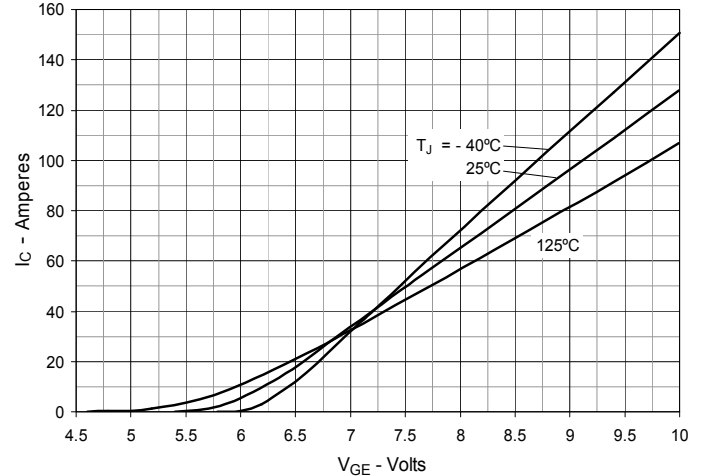


Fig. 7. Transconductance

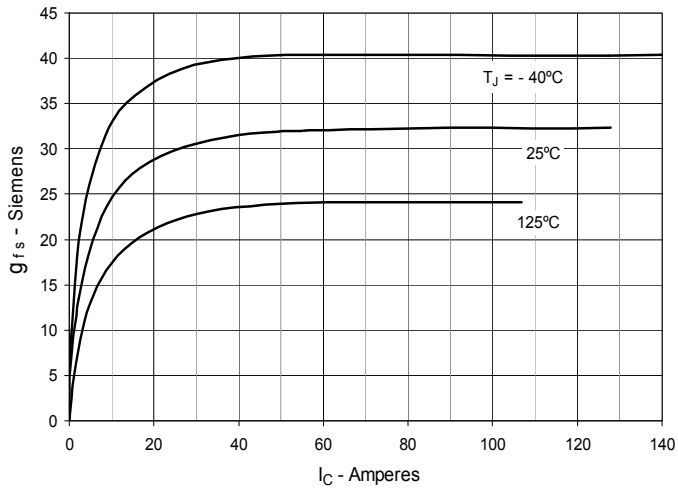


Fig. 8. Gate Charge

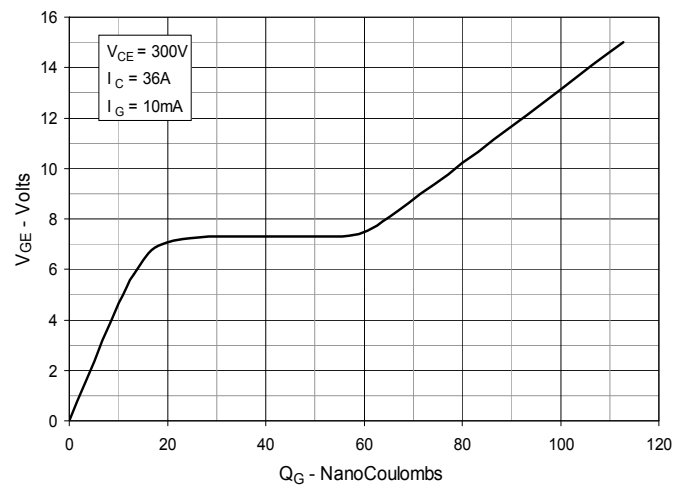


Fig. 9. Capacitance

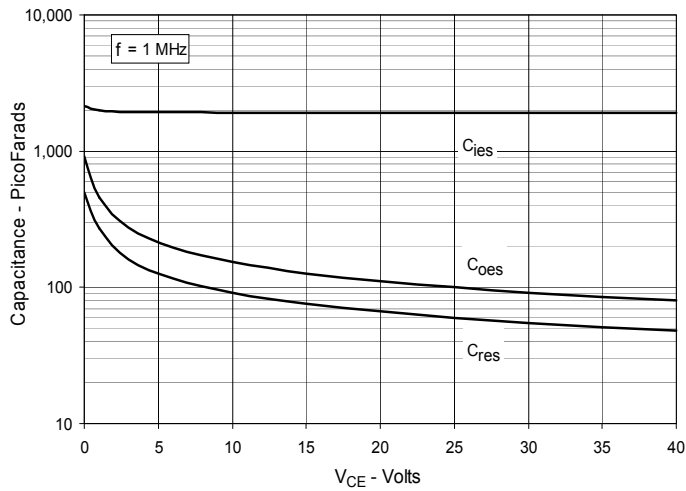


Fig. 10. Reverse-Bias Safe Operating Area

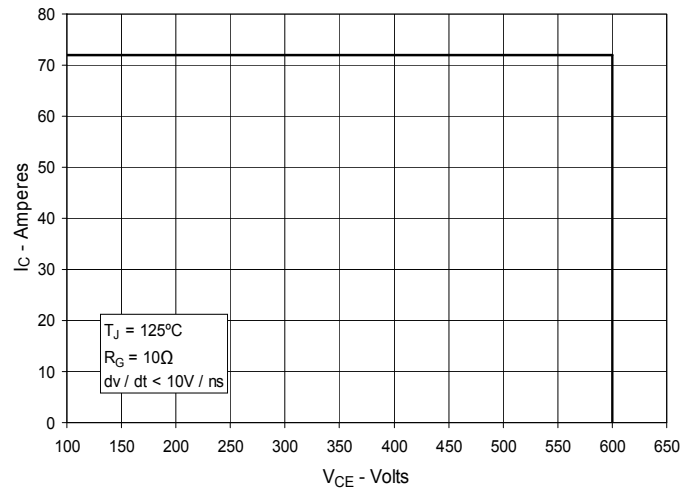


Fig. 11. Maximum Transient Thermal Impedance

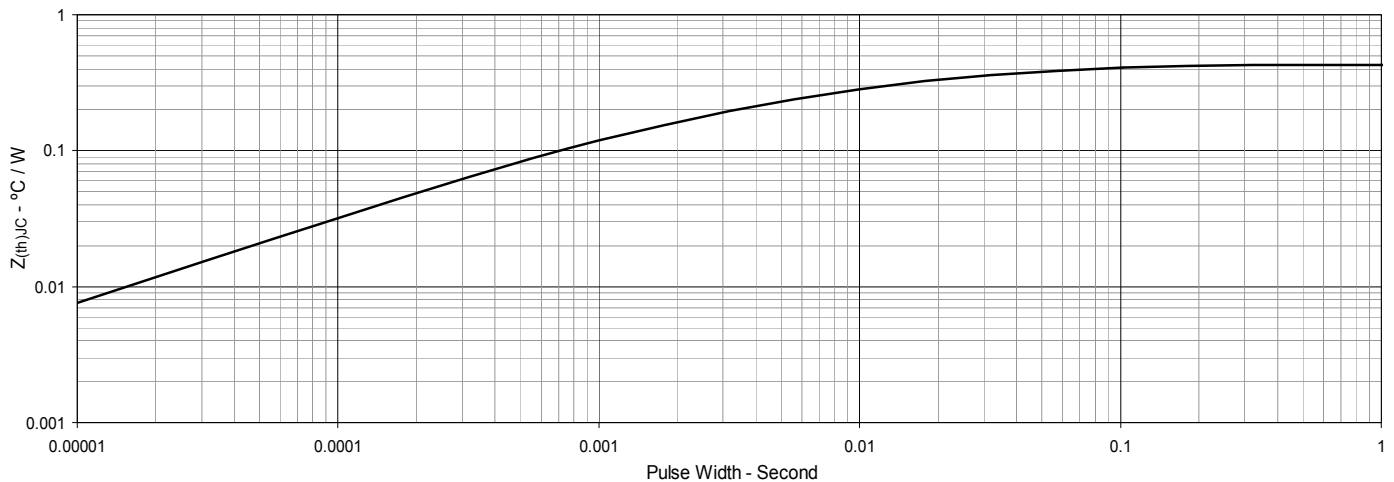


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

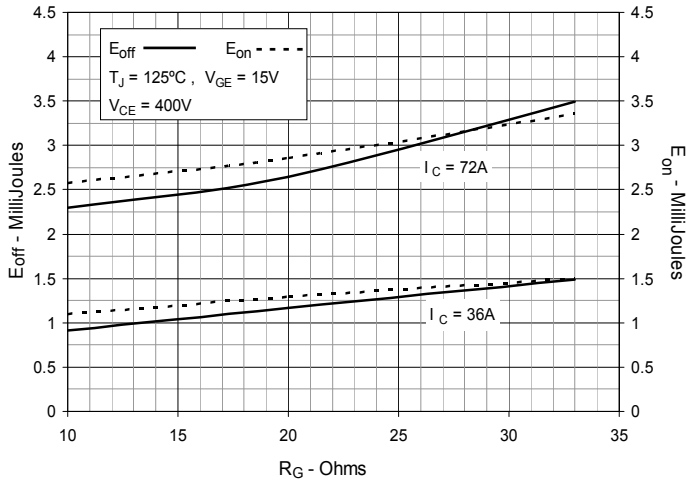


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

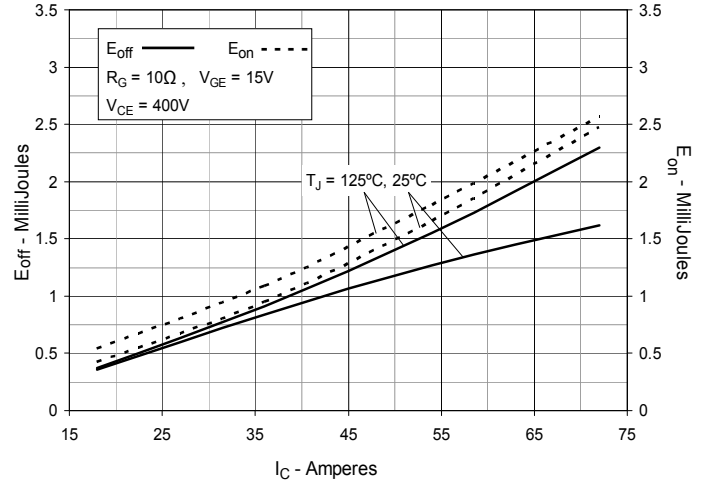


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

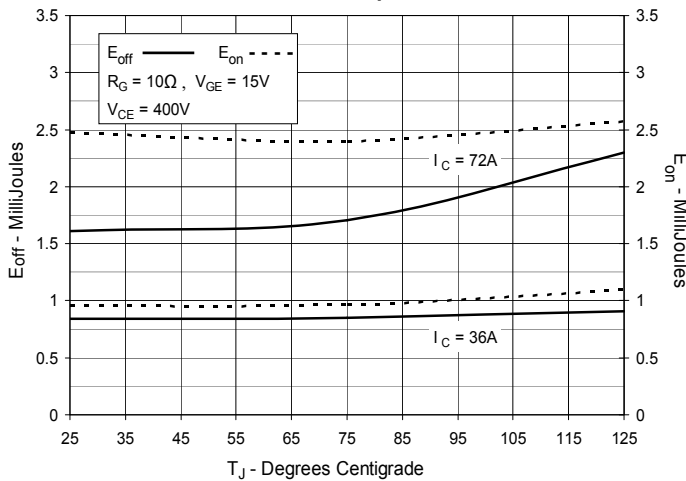


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

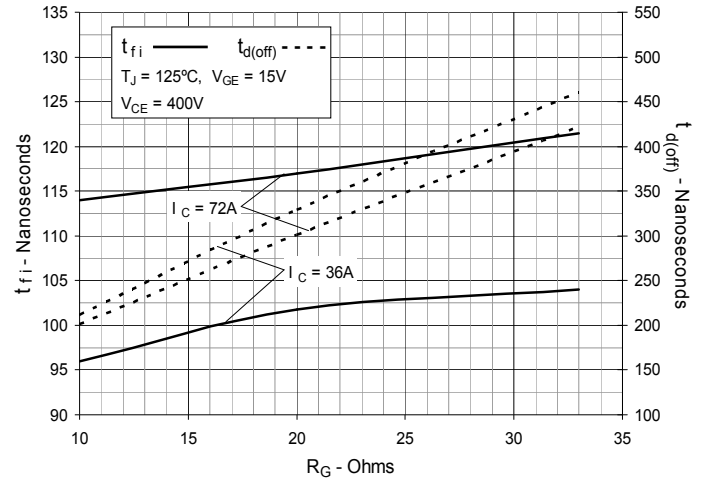


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

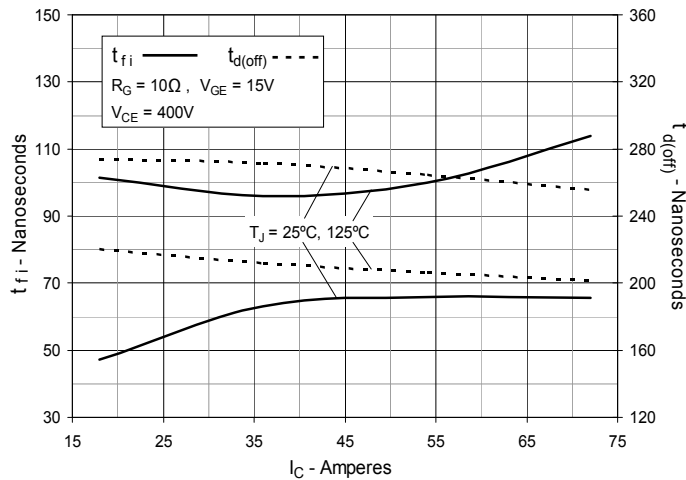


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

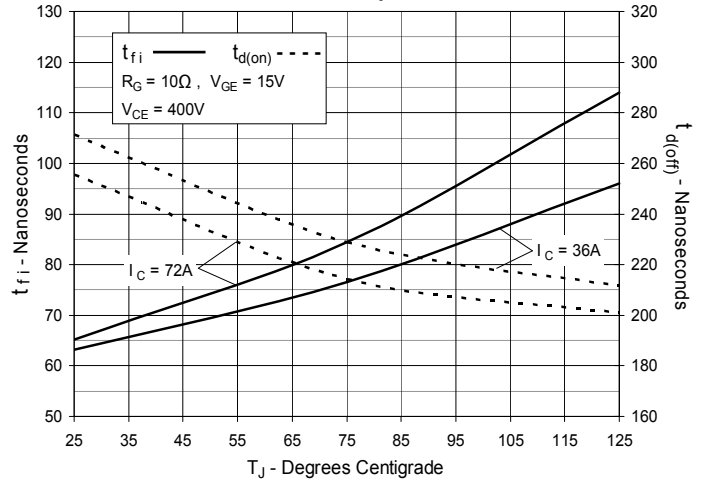


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

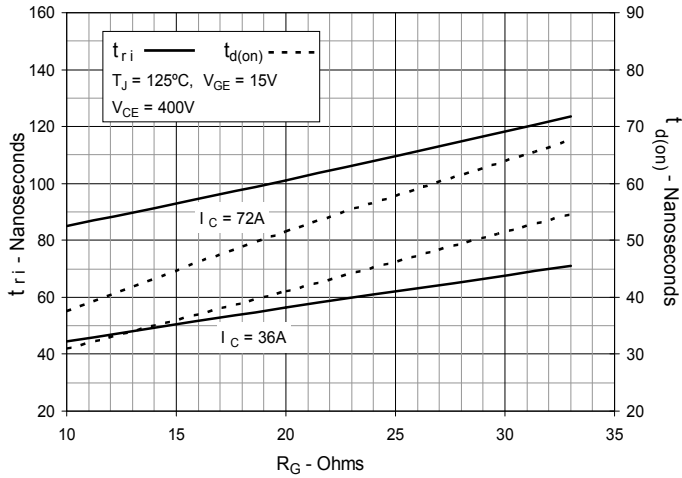


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

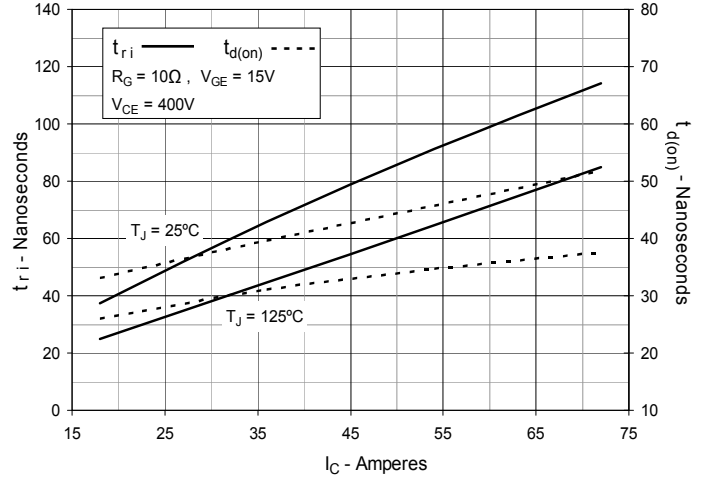


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

